



SSC2500GN1

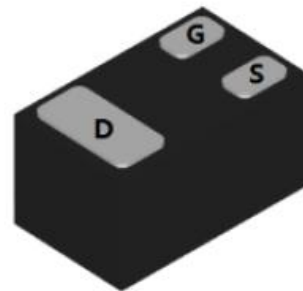
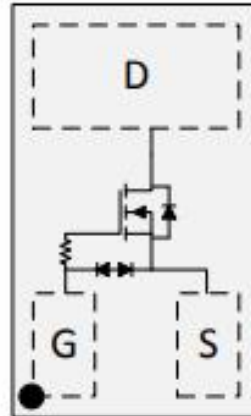
N-Channel Enhancement Mode MOSFET with ESD protection

➤ Features

| VDS | VGS | RDSON Typ. | ID | ESD |
|-----|-----|------------|------|-----|
| 20V | ±8V | 195mR@4V5 | 1.1A | 2K |
| | | 240mR@2V5 | | |
| | | 305mR@1V8 | | |

➤ Pin configuration

Top view



Bottom View

➤ Description

This device is a N-Channel enhancement mode MOSFET which is produced with high cell density and DMOS trench technology. This device particularly suits low voltage applications, especially for battery powered circuits, the tiny and thin outline saves PCB consumption.

➤ Applications

- Load Switch
- Portable Devices
- DCDC conversion

➤ Ordering Information

| Device | Package | Shipping |
|------------|---------|----------|
| SSC2500GN1 | DFN1006 | 10K/Reel |



Marking



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol | Parameter | Ratings | Unit |
|-----------|---------------------------------------|------------|--------------------|
| V_{DSS} | Drain-to-Source Voltage | 20 | V |
| V_{GSS} | Gate-to-Source Voltage | ± 8 | V |
| I_D | Continuous Drain Current ^a | 1.1 | A |
| I_{DM} | Pulsed Drain Current ^b | 3.1 | A |
| P_D | Power Dissipation ^c | 0.32 | W |
| P_{DSM} | Power Dissipation ^a | 0.18 | W |
| T_J | Operation junction temperature | -55 to 150 | $^{\circ}\text{C}$ |
| T_{STG} | Storage temperature range | -55 to 150 | $^{\circ}\text{C}$ |

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol | Parameter | Typical | Maximum | Unit |
|-----------------|--|---------|---------|-----------------------------|
| $R_{\theta JA}$ | Junction-to-Ambient Thermal Resistance ^a | | 690 | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JC}$ | Junction-to-Case Thermal Resistance | | 379 | |

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user is specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_J(\text{MAX})=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

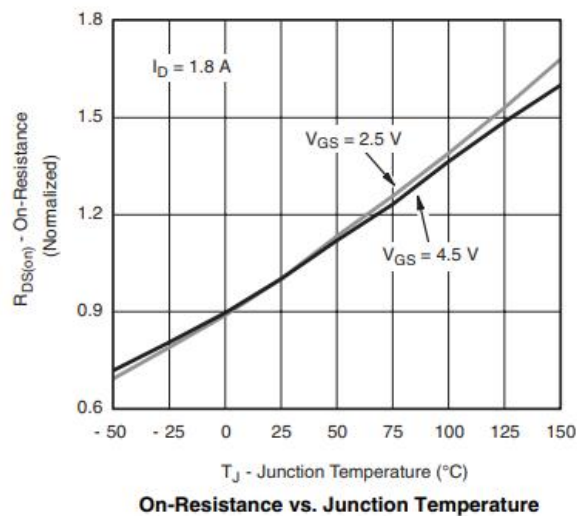
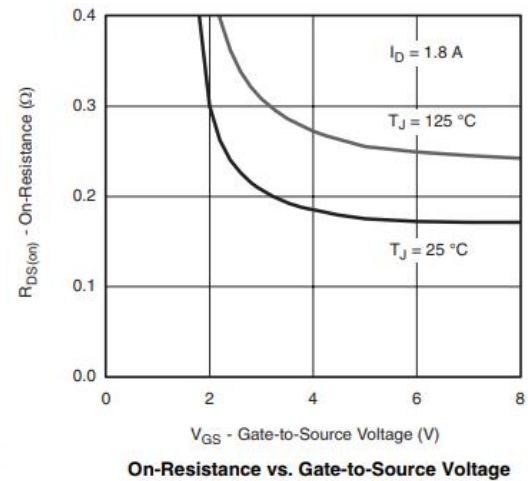
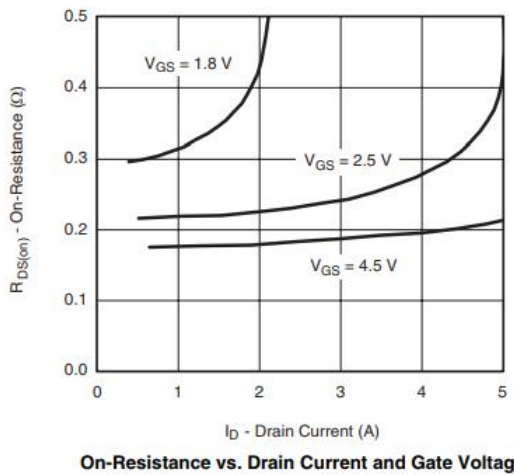
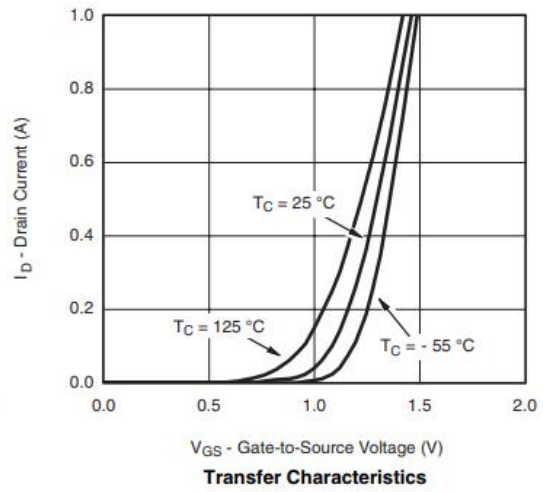
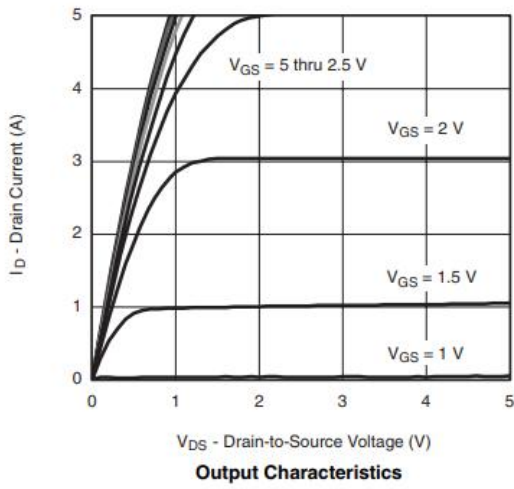


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ. | Max | Unit |
|---------------|------------------------------------|--|-----|------|----------|---------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$ | 20 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.5 | 0.68 | 1 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | $V_{GS}=4.5V, I_D=0.5A$ | | 195 | 310 | mR |
| | | $V_{GS}=2.5V, I_D=0.5A$ | | 240 | 380 | |
| | | $V_{GS}=1.8V, I_D=0.35A$ | | 305 | 800 | |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=20V, V_{GS}=0V$ | | | 1 | μA |
| I_{GSS} | Gate-Source leak current | $V_{GS}=\pm 8V, V_{DS}=0V$ | | | ± 10 | μA |
| G_{FS} | Forward Transconductance | $V_{DS}=5V, I_D=0.5A$ | | 2 | | S |
| V_{SD} | Forward Voltage | $V_{GS}=0V, I_S=0.5A$ | | 0.7 | 1.3 | V |
| C_{iss} | Input Capacitance | $V_{DS}=10V, V_{GS}=0V,$ $F=1\text{MHZ}$ | | 66 | | pF |
| C_{oss} | Output Capacitance | | | 18 | | |
| C_{rss} | Reverse Transfer Capacitance | | | 9 | | |
| $T_{D(ON)}$ | Turn-on delay time | $V_{GS}=4.5V,$ $V_{DS}=10V, R_G=6R, I_D=0.6A$ | | 20 | | ns |
| $T_{D(OFF)}$ | Turn-off delay time | | | 40 | | |

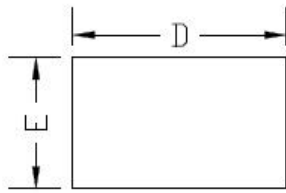


➤ Typical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

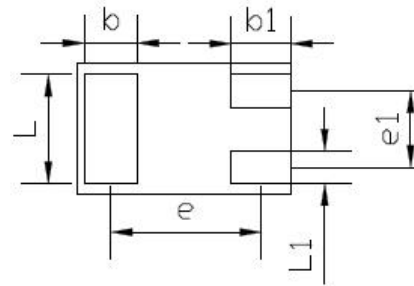




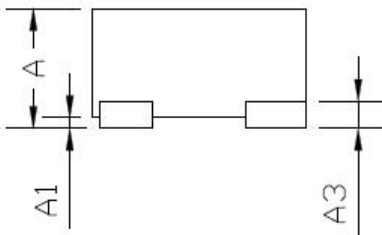
➤ Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

| COMMON DIMENSION (MM) | | | |
|-----------------------|-----------|------|------|
| PKG | DFN1006 | | |
| REF. | MIN. | NOM. | MAX |
| A | >0.4 | - | 0.50 |
| A1 | 0.00 | - | 0.05 |
| A3 | 0.125REF. | | |
| D | 0.95 | 1.00 | 1.05 |
| E | 0.55 | 0.60 | 0.65 |
| b | 0.20 | 0.25 | 0.30 |
| b1 | 0.20 | 0.30 | 0.40 |
| L | 0.45 | 0.50 | 0.55 |
| L1 | 0.10 | 0.15 | 0.20 |
| e | 0.675 | | |
| e1 | 0.35 | | |

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